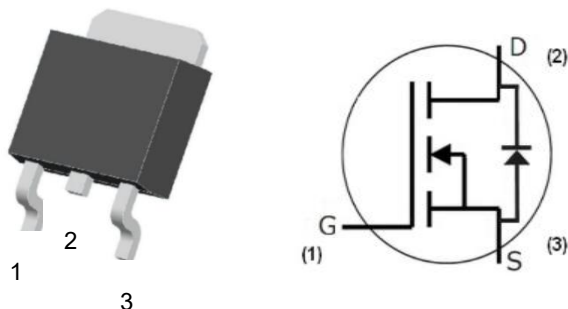


SiC MOSFET

800V 1400mΩ typ. @ $V_{GS}=18V$, $T_j=25^{\circ}C$
 800V 2600mΩ typ. @ $V_{GS}=12V$, $T_j=150^{\circ}C$
 Silicon Carbide Power MOSFET
 N-Channel Enhancement Mode



Features

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Q_{rr})
- Halogen free, RoHs compliant

Benefits

- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

Applications

- Switch mode power supplies
- Renewable energy
- PD Charger
- High voltage DC/DC converters

Package Pin Definitions

- Pin1- Gate
- Pin2- Drain
- Pin3- Source

Package Parameters

Part Number	Marking	Package
CI7N80E3	CI7N80E3	TO-252

Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V_{DSmax}	Drain-Source Voltage	$V_{GS} = 0\text{V}$, $I_D = 100\mu\text{A}$	800	V	
V_{GS}	Gate-Source voltage (transient)	$t_p \leq 500\text{ns}$, duty cycle $\leq 1\%$	-12/+22	V	
V_{GSop}	Recommend Gate-Source Voltage	Static	-4/+18	V	
$V_{GSop,max}$	Maximum recommend Gate-Source Voltage		-5/+20	V	
EAS	Single pulse avalanche energy	$V_{DS}=800\text{V}$, $V_{DD}=50\text{V}$, $V_{GS}=15\text{V}$, $L=1\text{mH}$, $T_C=25^{\circ}\text{C}$	12.5	mJ	
I_D	Continuous Drain current ¹⁾	$V_{GS} = 18\text{V}$, $T_C = 25^{\circ}\text{C}$	7	A	Fig. 14
		$V_{GS} = 18\text{V}$, $T_C = 100^{\circ}\text{C}$	4.9		
I_{DM}	Pulsed Drain Current ²⁾	Pulse width t_p limited by T_{jmax}	12.5	A	
P_D	Power Dissipation	$T_C = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	30	W	Fig. 16
T_j	Operating junction temperature		-55~150	$^{\circ}\text{C}$	
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$	

Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		5.0		$^{\circ}\text{C/W}$	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		$^{\circ}\text{C/W}$	

Electrical Characteristics $T_j=25^{\circ}\text{C}$ unless otherwise specified

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0V, I_D = 100\mu A$	800			V	
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 0.4mA$	2.0	2.7	4.0	V	Fig. 9
		$V_{GS} = V_{DS}, I_D = 0.4mA, T_j = 150^{\circ}\text{C}$		2.0			
I_{GSS}	Gate-Source Leakage current	$V_{GS} = 15V, V_{DS} = 0V$			250	nA	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V, T_j = 25^{\circ}\text{C}$		1	50	μA	
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 12V, I_D = 0.5A$		3300	2000	m Ω	Fig. 3, 4, 5
		$V_{GS} = 15V, I_D = 0.5A$		1650			
		$V_{GS} = 18V, I_D = 0.5A$		1400			
		$V_{GS} = 12V, I_D = 0.5A, T_j = 150^{\circ}\text{C}$		2600			
g_{fs}	Transconductance	$V_{DS} = 15V, I_D = 0.5A$		0.21		S	Fig. 6
		$V_{DS} = 15V, I_D = 0.5A, T_j = 150^{\circ}\text{C}$		0.2			

Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q_{GS}	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 0.5A$ $V_{GS} = -4V/15V$		1.1		nC	Fig. 10
Q_{GD}	Gate to Drain Charge			2.7			
Q_G	Total Gate Charge			4.5			

AC Characteristics ($T_J=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1\text{ MHz}$ $V_{AC} = 25mV$		37.5		pF	Fig. 13
C_{oss}	Output Capacitance			11.5		pF	
C_{rss}	Reverse Transfer Capacitance			1.9		pF	
$R_{G(int)}$	Internal Gate Resistance	$f=1\text{ MHz}, V_{AC} = 25mV$		15		Ω	

Reverse Diode Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	$V_{GS} = -4\text{V}, I_{SD} = 0.25\text{A}$		4.4		V	Fig. 7,8
		$V_{GS} = -4\text{V}, I_{SD} = 0.25\text{A}, T_J = 150^{\circ}\text{C}$		3.8			
I_S	Continuous Diode Forward Current	$V_{GS} = -4\text{V}, T_C = 25^{\circ}\text{C}$		6.2		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4\text{V}$, pulse width t_p limited by T_{Jmax}		12.5		A	
t_{rr}	Reverse Recovery Time	$V_{GS} = -4\text{V}, I_{SD} = 0.5\text{A}, V_R = 400\text{V}$ $\text{dif/dt} = 1000\text{A/us}$		24		nS	
Q_{rr}	Reverse Recovery Charge			25		nC	
I_{rm}	Peak Reverse Recovery Current			2.3		A	

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400\text{V}, V_{GS} = -4/+15\text{V}$ $I_D = 0.5\text{A}, R_{G(ext)} = 20\Omega$ $L = 2.4\text{mH}$		2		nS	Fig.21
t_r	Rise Time			6		nS	
$t_{d(off)}$	Turn-Off Delay Time			8		nS	
t_f	Fall Time			98		nS	
E_{on}	Turn-On Energy			3		μJ	Fig.19
E_{off}	Turn-Off Energy			3		μJ	
E_{tot}	Total switching energy			6		μJ	

Note:

1) Calculated continuous current based on maximum allowable junction temperature.

2) Repetitive rating; pulse width limited by max. junction temperature.

Typical Performance

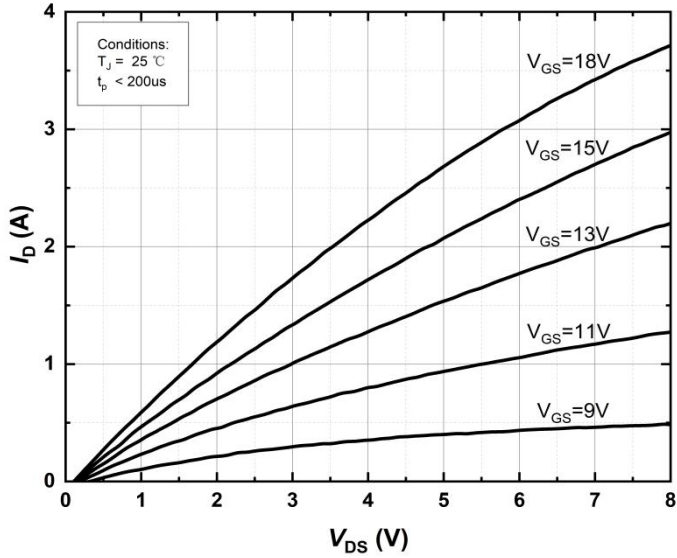


Figure 1. Output characteristics at $T_j=25^{\circ}\text{C}$

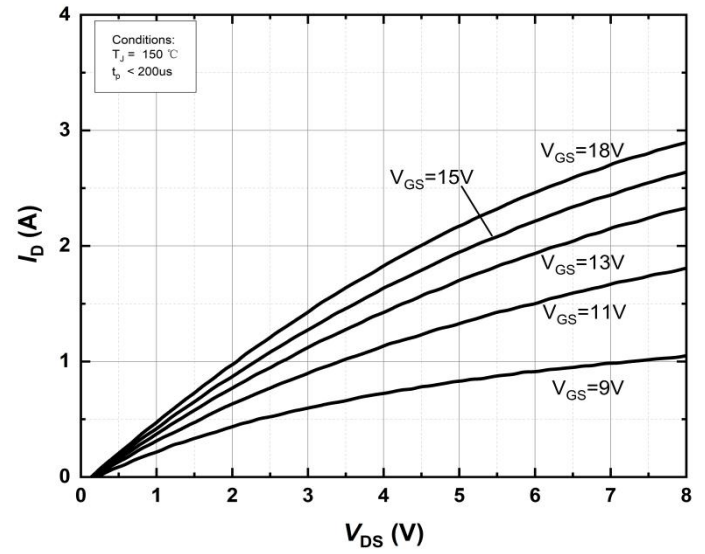


Figure 2. Output characteristics at $T_j=150^{\circ}\text{C}$

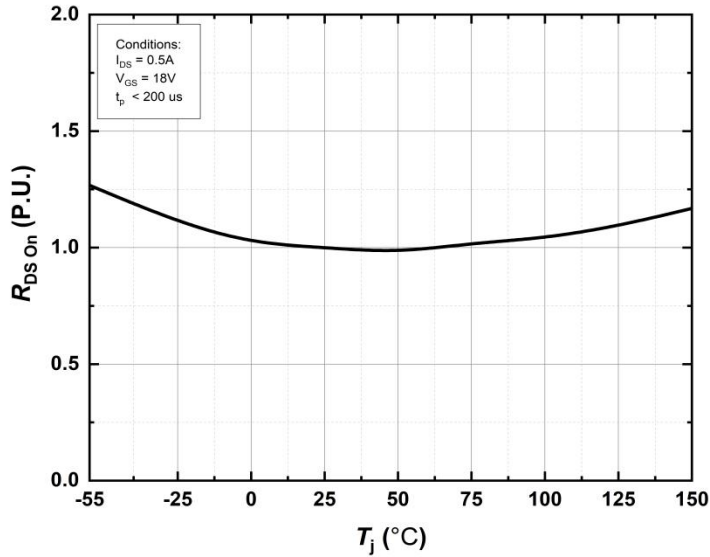


Figure 3. Normalized On-Resistance vs. Temperature

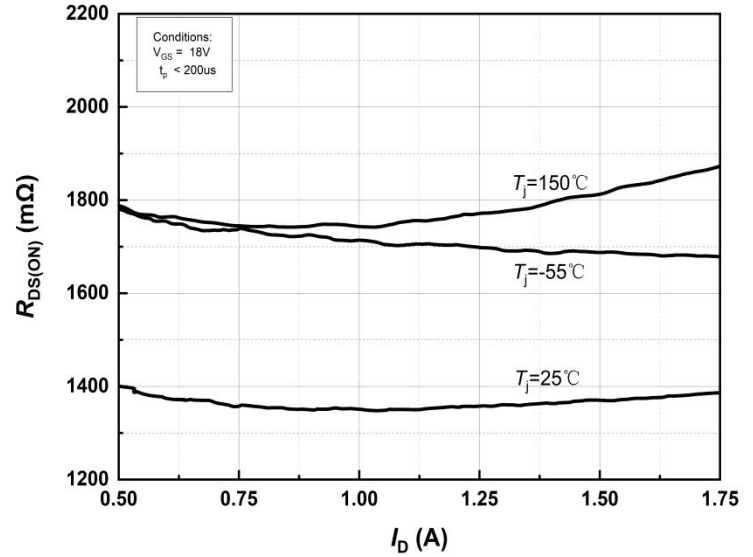


Figure 4. On-Resistance vs. Drain current for Various Temperature

Typical Performance

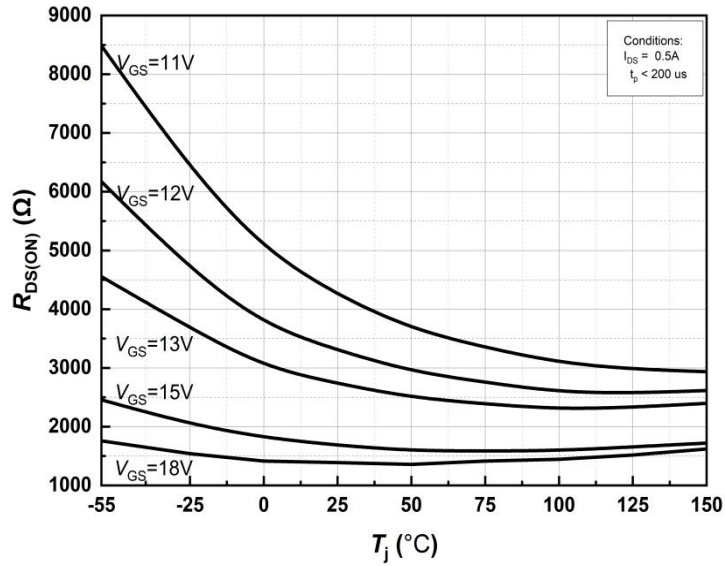


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

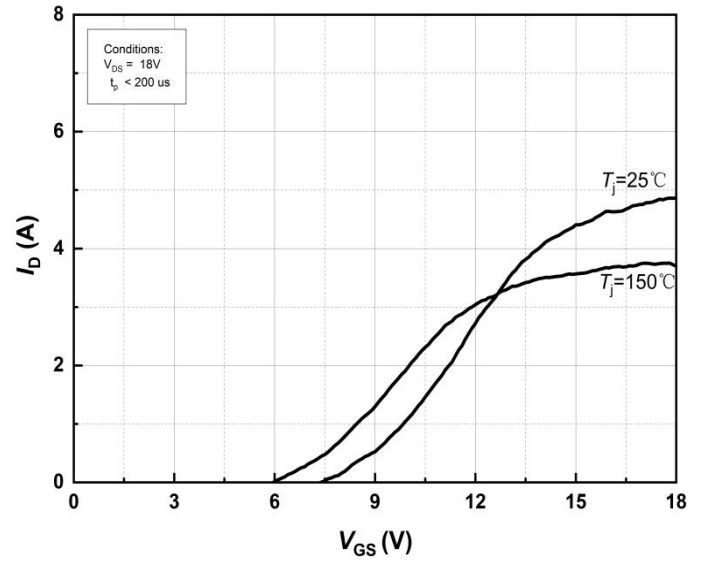


Figure 6. Transfer Characteristics for Various Junction Temperatures

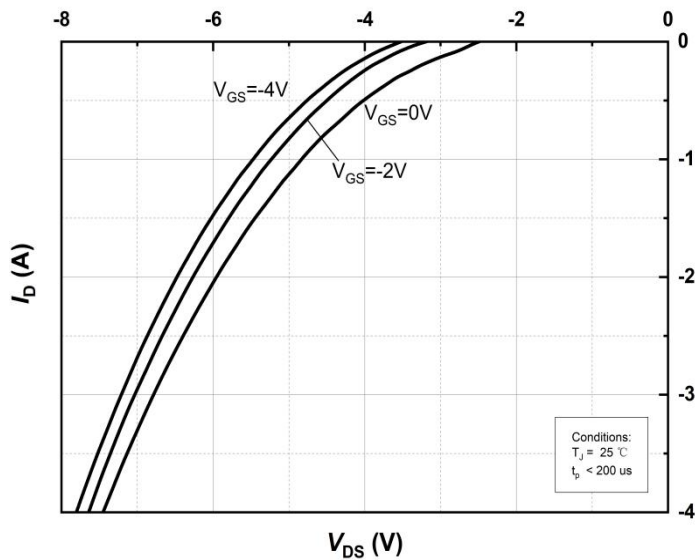


Figure 7. Body Diode Characteristics at $T_j=25^{\circ}\text{C}$

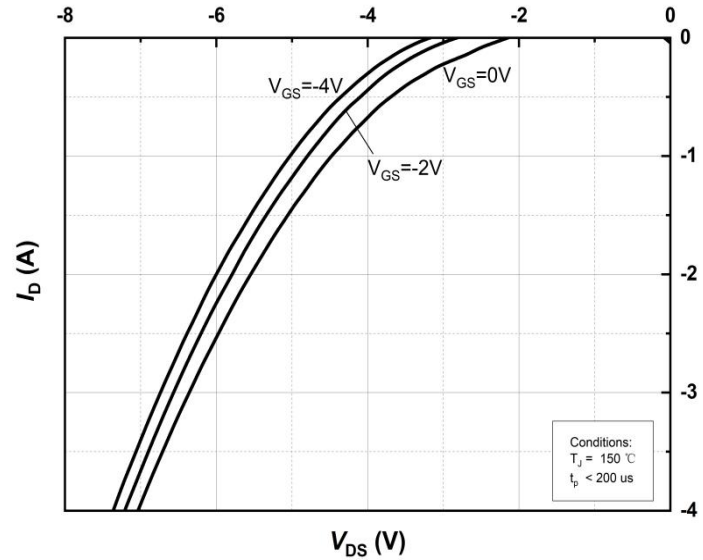


Figure 8. Body Diode Characteristics at $T_j=150^{\circ}\text{C}$

Typical Performance

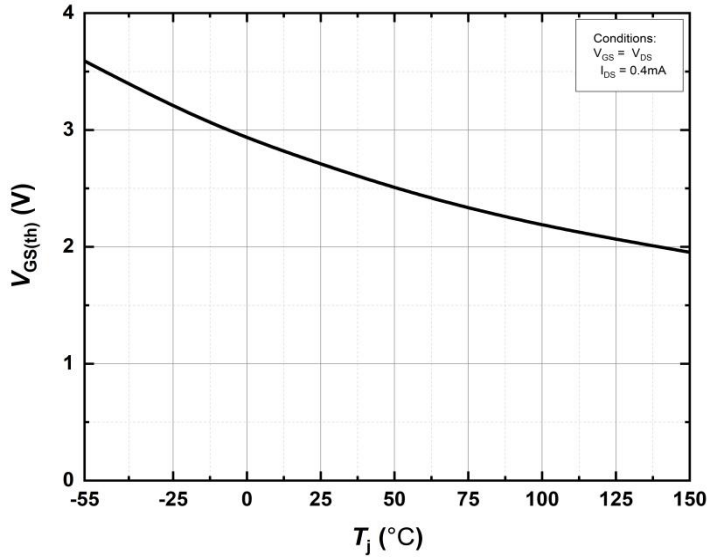


Figure 9. Threshold Voltage vs. Temperature

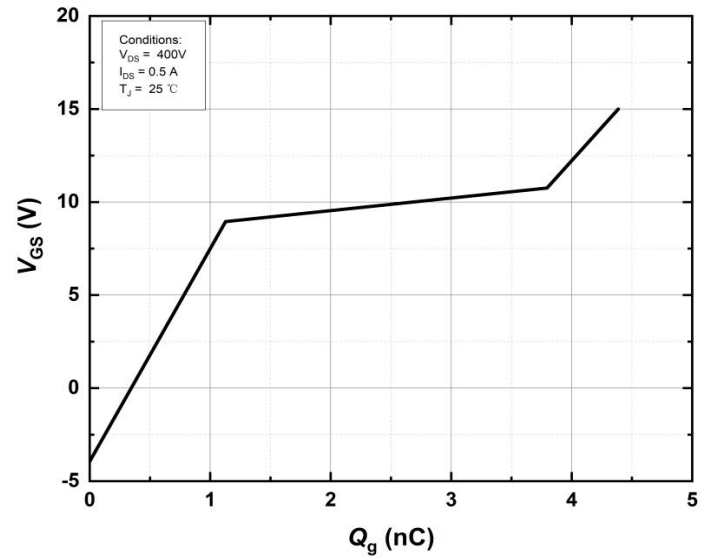


Figure 10 Gate Charge Characteristics

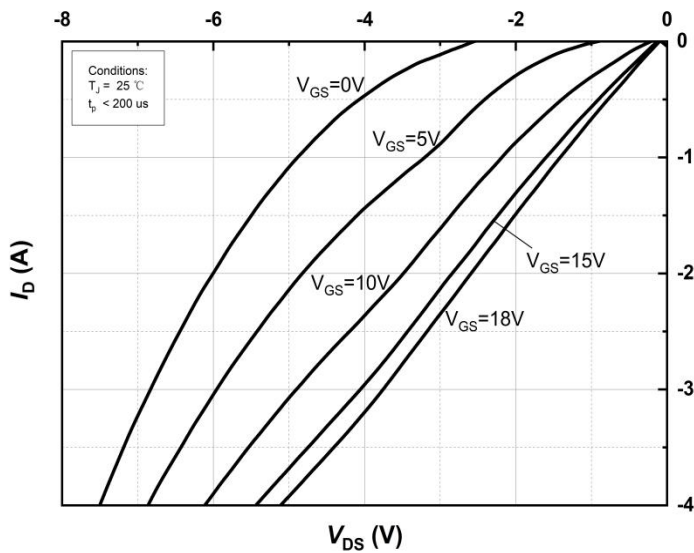


Figure 11. 3rd Quadrant Characteristic at $T_J=25^\circ C$

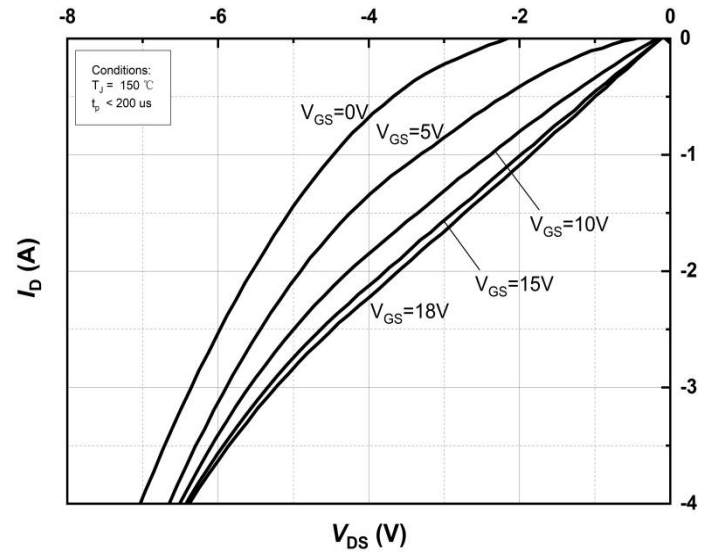


Figure 12. 3rd Quadrant Characteristic at $T_J=150^\circ C$

Typical Performance

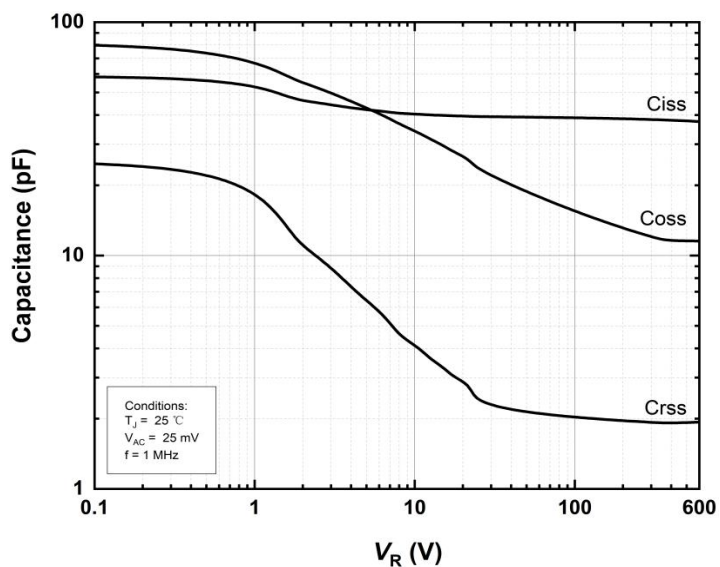


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

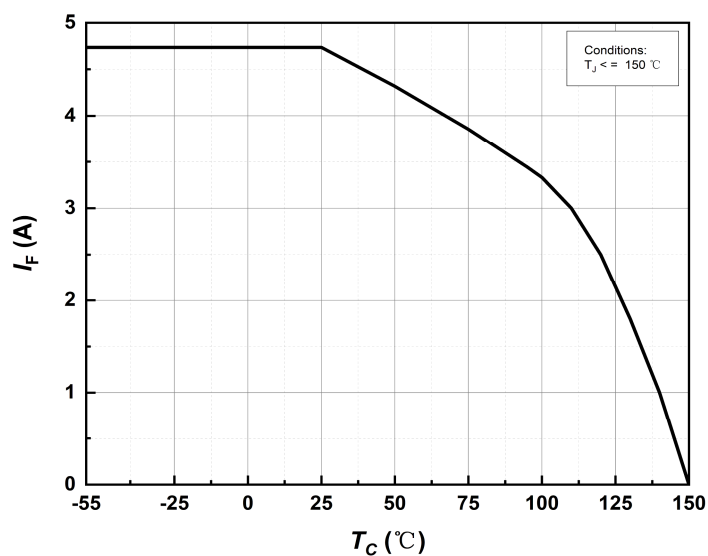


Figure 14. Continuous Drain Current Derating vs Case Temperature

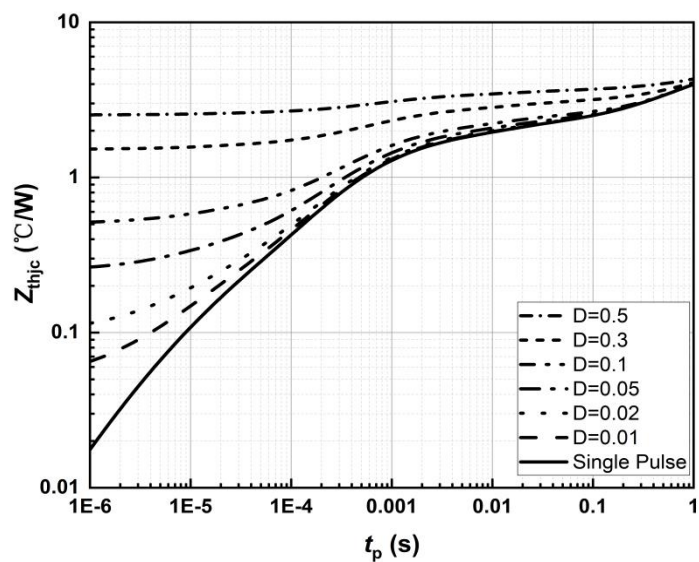


Figure 15. Transient Thermal Impedance (Junction – Case)

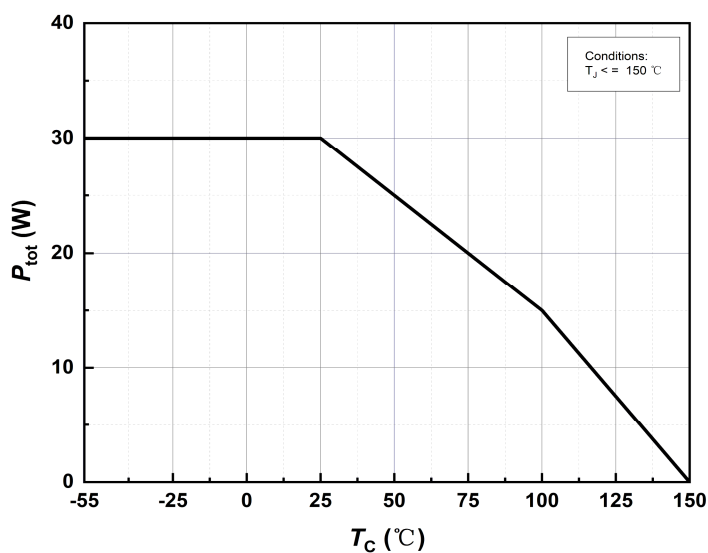


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

Typical Performance

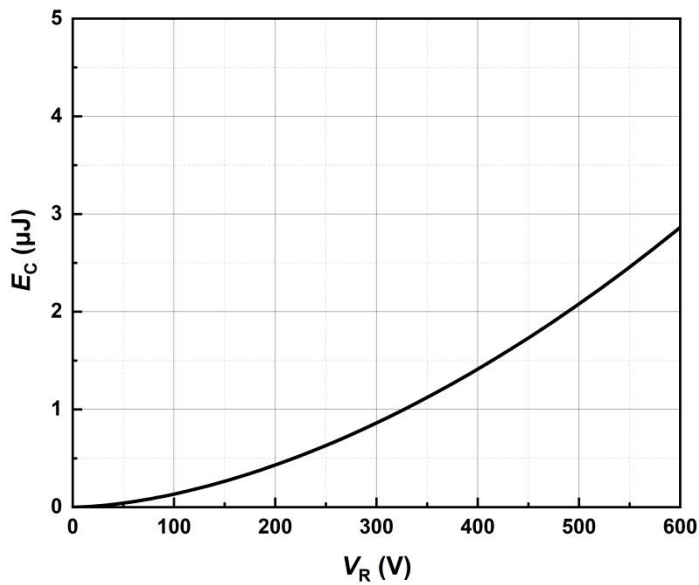


Figure 17. Output Capacitor Stored Energy

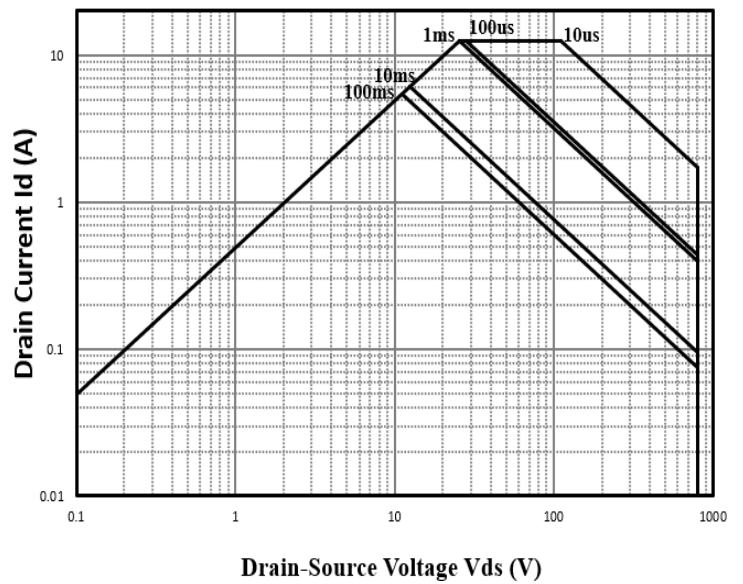


Figure 18. Safe Operating Area

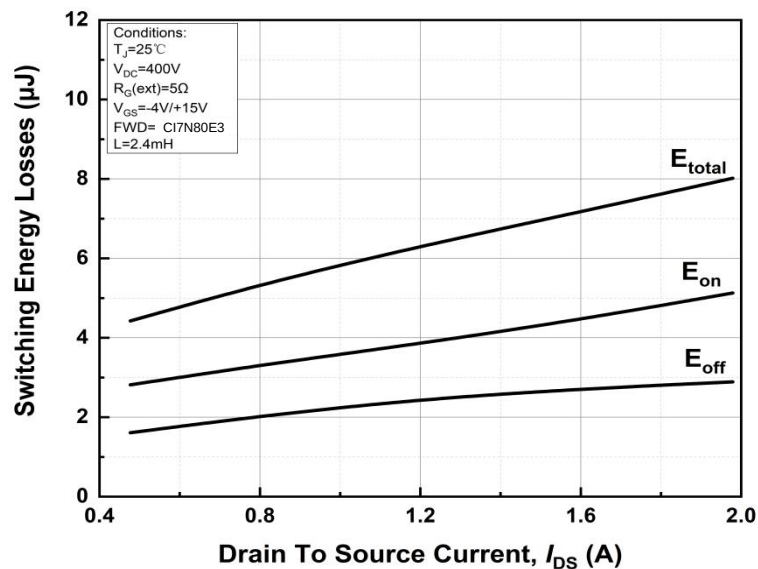


Figure 19. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 400\text{V}$)

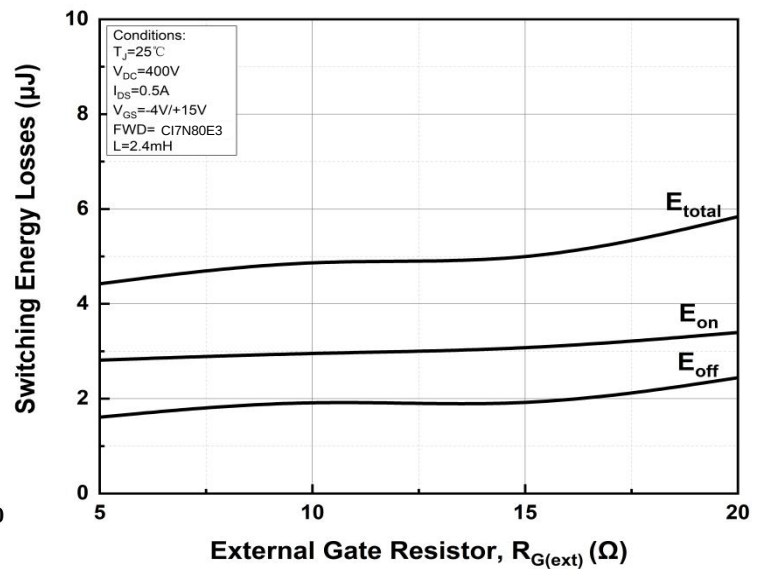


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(\text{ext})}$

Typical Performance

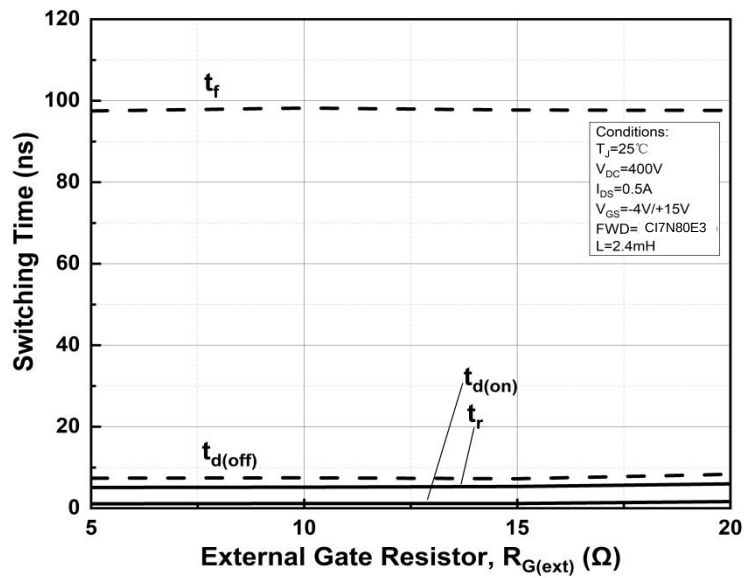
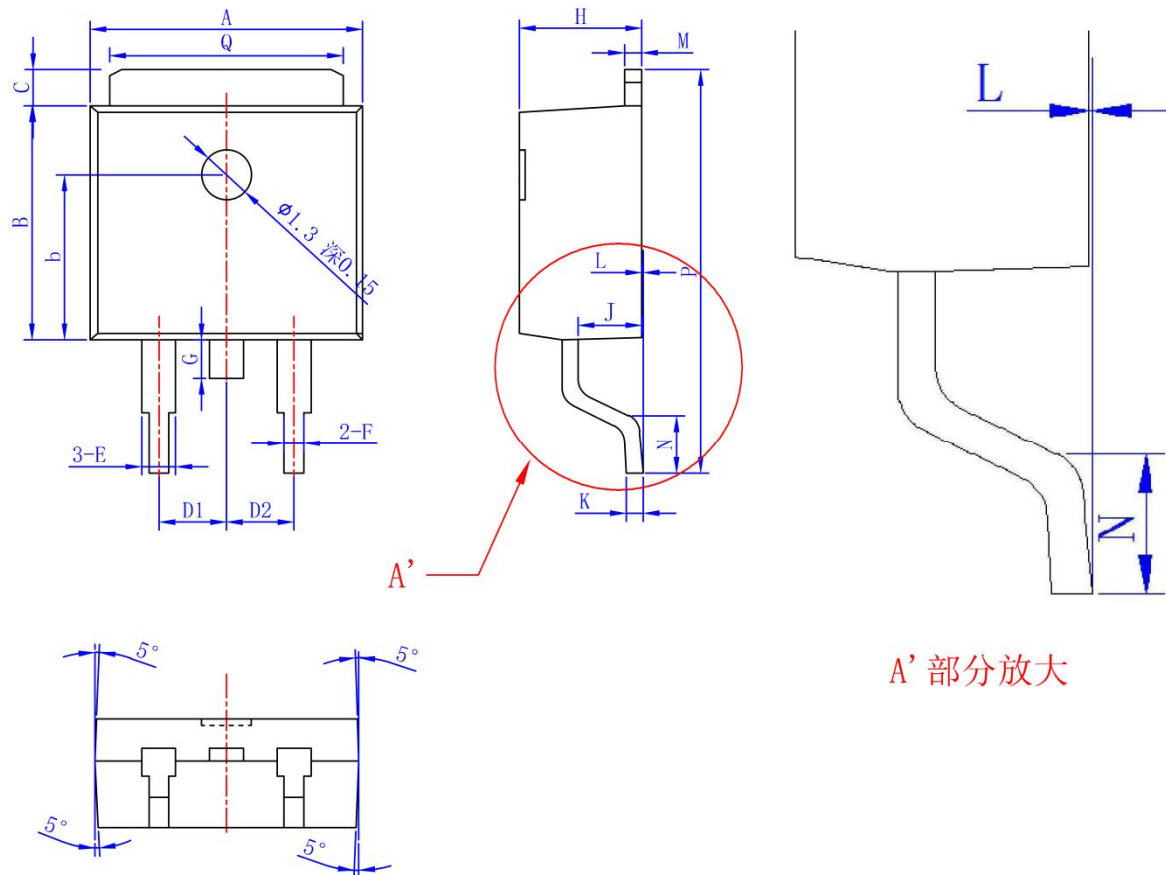


Figure 21. Switching Times vs. $R_{G(ext)}$

Package Dimensions



A' 部分放大

SYMBOL	MM		
	MIN	NOM	MAX
*A	6.30	6.55	6.90
*B	5.90	6.10	6.30
b	4.10	4.30	4.50
C	0.90	1.00	1.10
*D1		2.29BSC	
*D2		2.29BSC	
*E	0.61	0.76	0.91
*F	0.50	0.60	0.70
G	0.60	0.80	1.00
*H	2.10	2.30	2.50
*J	0.90	1.00	1.10
*K	0.40	0.50	0.60
*L	0.00	0.05	0.127
*M	0.45	0.50	0.55
*N	1.39		1.77
*P	9.60	9.90	10.30
Q	5.10	5.30	5.50
带*为必须检验尺寸			